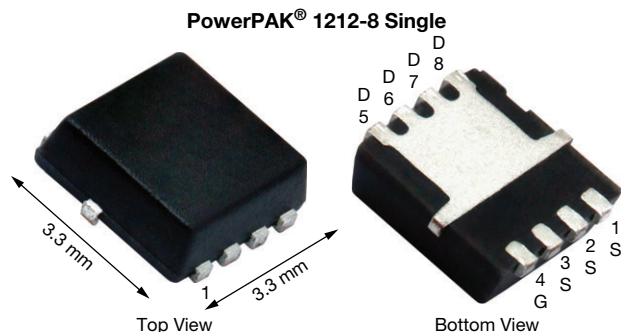


N-Channel 30 V (D-S) MOSFET



RoHS
COMPLIANT
HALOGEN
FREE



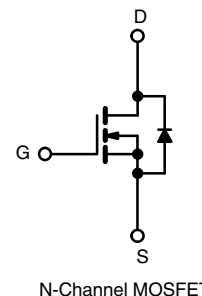
PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.0067
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.0100
Q_g typ. (nC)	8.3
I_D (A)	40.5
Configuration	Single

FEATURES

- TrenchFET® Gen IV power MOSFET
- 100 % R_g and UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912

APPLICATIONS

- DC/DC conversion
- Battery protection
- Load switching
- DC/AC inverters



N-Channel MOSFET

ORDERING INFORMATION

Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSA88DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	+20, -16	
Continuous drain current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed drain current ($t = 300$ μ s)	I_{DM}	100	A
Continuous source-drain diode current	I_S	18	
		2.9 ^{b, c}	
Single pulse avalanche current	I_{AS}	10	mJ
Single pulse avalanche energy	E_{AS}	5	
Maximum power dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{b, f}	R_{thJA}	31	39	°C/W
Maximum junction-to-case (drain)	R_{thJC}	5	6.3	

Notes

- Based on $T_C = 25$ °C
- Surface mounted on 1" x 1" FR4 board
- $t = 10$ s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 81 °C/W



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V	
Drain-source breakdown voltage (transient) ^c	V _{DSt}	V _{GS} = 0 V, I _{D(aval)} = 10 A, t _{transcient} ≤ 50 ns	36	-	-		
V _{DS} temperature coefficient	ΔV _{DS} /T _J	I _D = 250 μA	-	15.5	-	mV/°C	
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J		-	-4.7	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1.1	-	2.4	V	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20, -16 V	-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	-	-	1	μA	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10		
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30	-	-	A	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A	-	0.0054	0.0067	Ω	
		V _{GS} = 4.5 V, I _D = 8 A	-	0.0078	0.0100		
Forward transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 10 A	-	47	-	S	
Dynamic ^{b, d}							
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	-	985	-	pF	
Input capacitance	C _{oss}		-	305	-		
Output capacitance	C _{rss}		-	38	-		
Reverse transfer capacitance			-	0.039	0.078		
C _{rss} /C _{iss} ratio	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A	-	16.8	25.5	nC	
Total gate charge		Q _{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A	-	8.3		12.5
Gate-source charge	Q _{gd}			-	2.1		-
Gate-drain charge	Q _{oss}			-	2.8		-
Gate-drain charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	-	8.7	-	Ω	
Output charge	R _g	f = 1 MHz	0.8	1.7	3.1		
Gate resistance	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	7	14		
Turn-on delay time	t _r		-	28	56		
Rise time	t _{d(off)}		-	14	28		
Turn-off delay time	t _f		-	8	16		
Fall time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	-	11	22		
Turn-on delay time	t _r		-	47	94		
Rise time	t _{d(off)}		-	18	36		
Turn-off delay time	t _f		-	18	36		
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	18	A	
Pulse diode forward current ^a	I _{SM}		-	-	100		
Body diode voltage	V _{SD}	I _S = 5 A	-	0.77	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	-	48	96	ns	
Body diode reverse recovery charge	Q _{rr}		-	72	140	nC	
Reverse recovery fall time	t _a		-	40	-	ns	
Reverse recovery rise time	t _b		-	8	-		

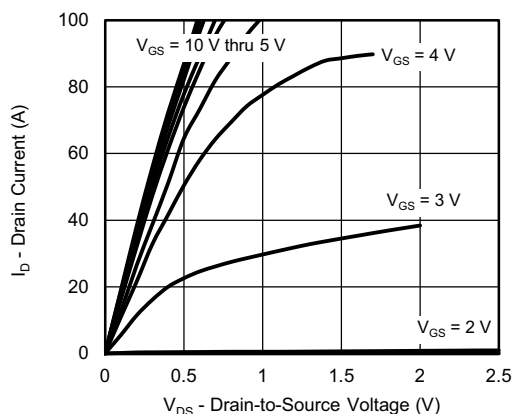
Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing
c. $T_C = 25\text{ }^{\circ}\text{C}$; expected voltage stress during 100 % UIS test. Production data log is not available

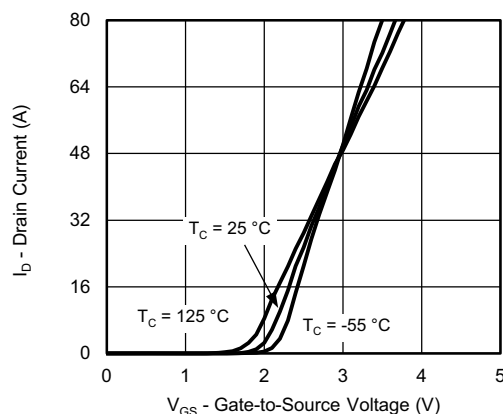
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



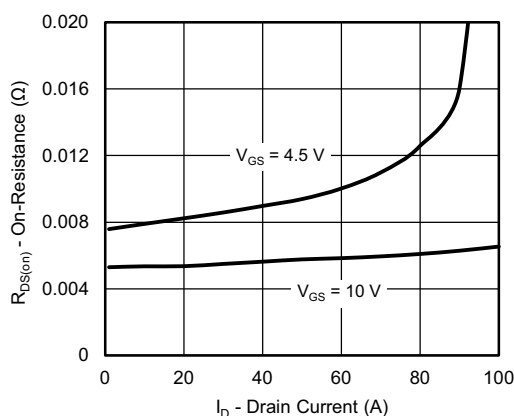
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



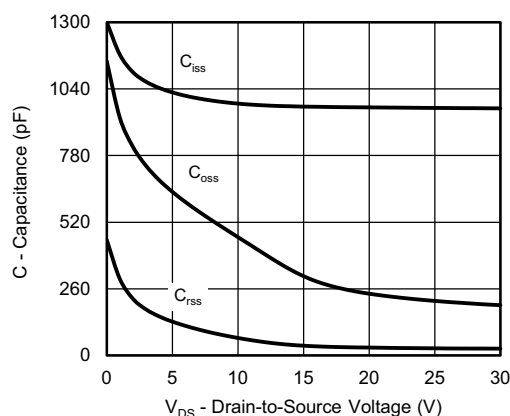
Output Characteristics



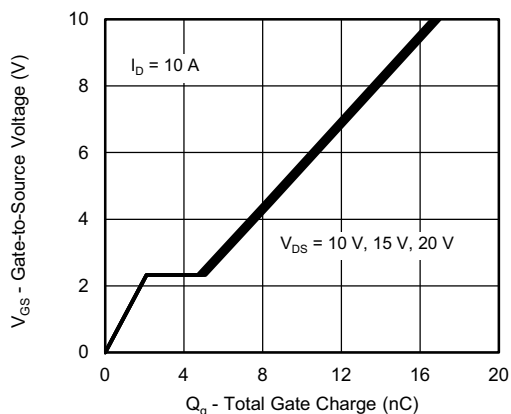
Transfer Characteristics



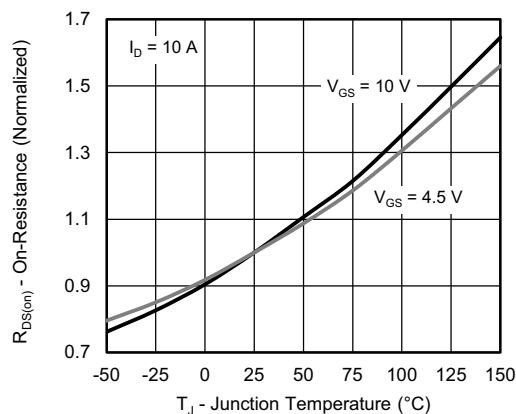
On-Resistance vs. Drain Current



Capacitance



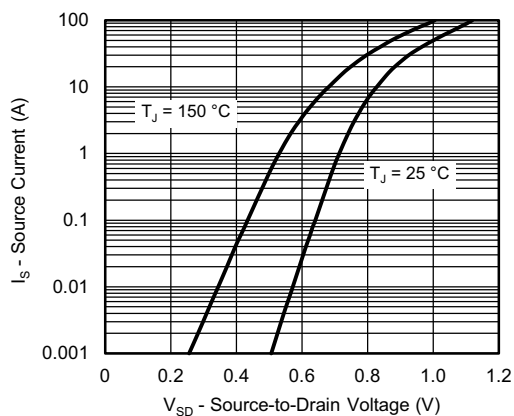
Gate Charge



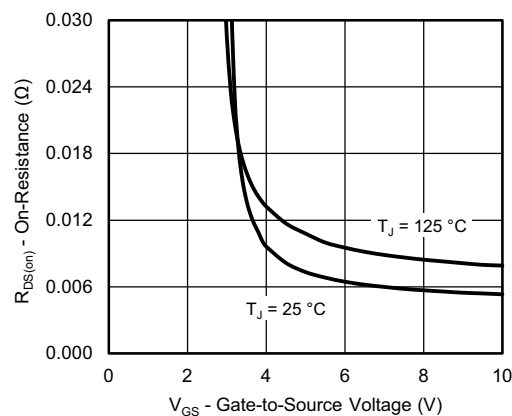
On-Resistance vs. Junction Temperature



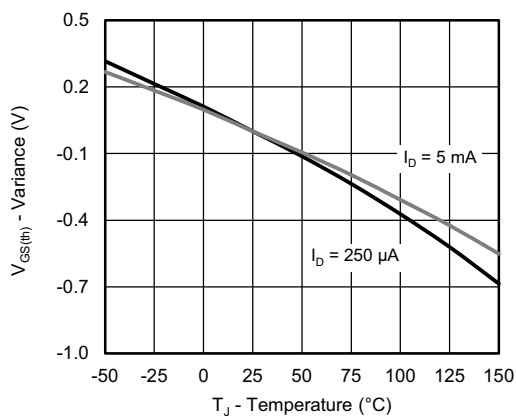
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



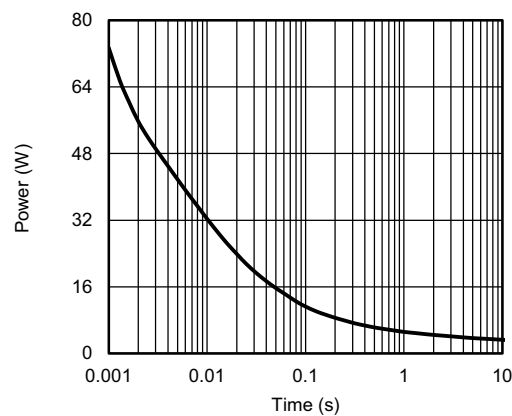
Source-Drain Diode Forward Voltage



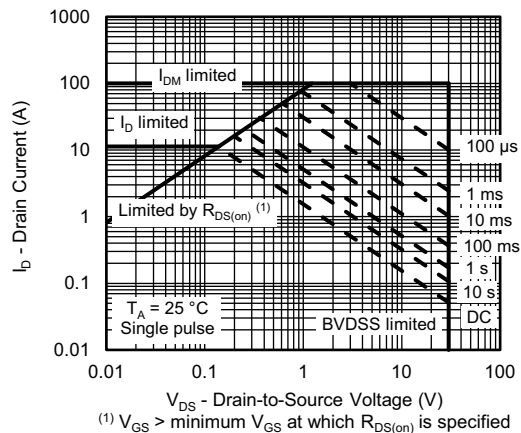
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



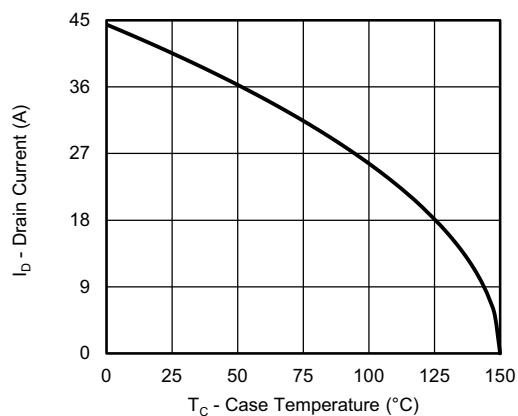
Single Pulse Power, Junction-to-Ambient



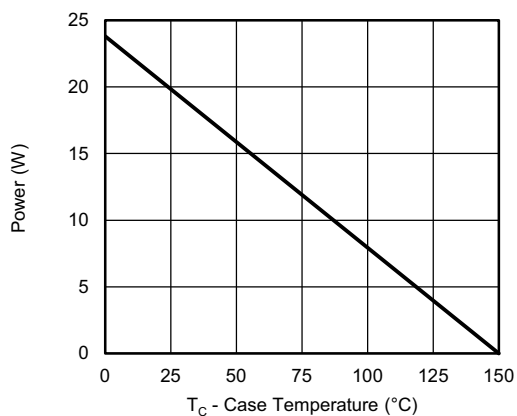
Safe Operating Area



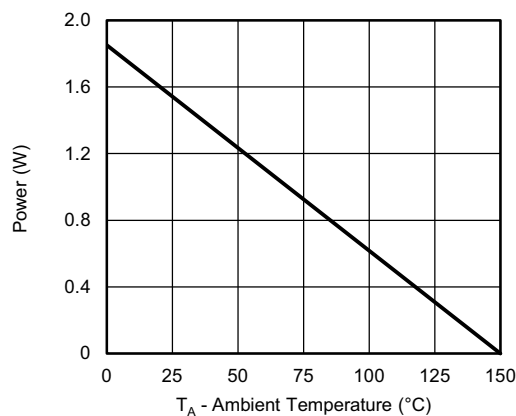
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case



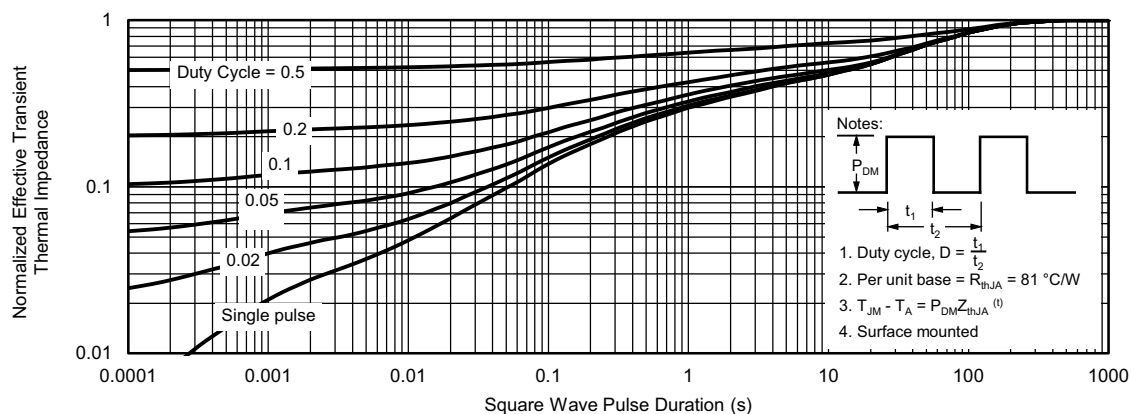
Power, Junction-to-Ambient

Note

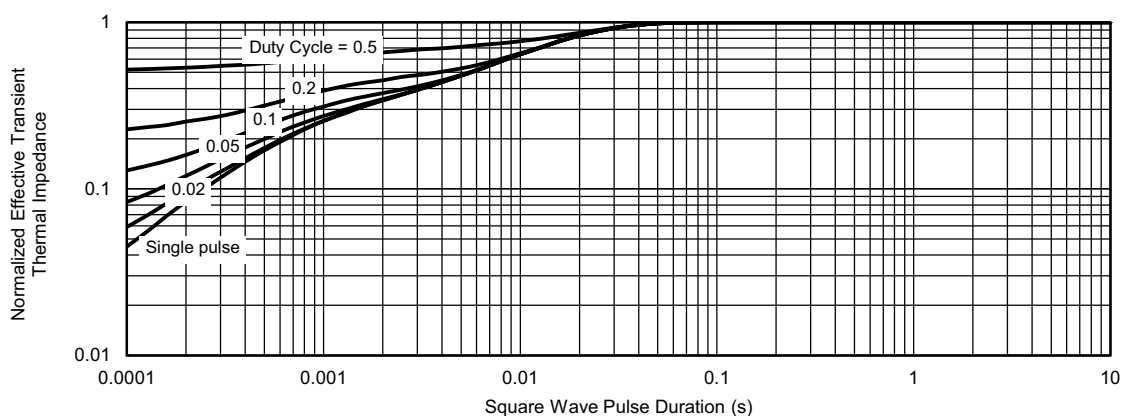
- a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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